Supporting Information for

Three-Phase Morphology Evolution in Sequentially Solution-Processed Polymer Photodetector: Towards Low Dark Current and High Photodetectivity

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## Photodetector characterization

For PPDs, the figures of merit which need to be evaluated include responsivity (R) and specific detectivity ( $D^*$ ). R is calculated by the ratio of the photocurrent to the intensity of the incident light as Eq. S1:

$$R(\lambda) = \frac{J_{ph}}{L_{light}} = EQE(\lambda)\frac{\lambda q}{hc}(A/W)$$
(S1)

where q is the electron charge,  $\lambda$  is the wavelength, h is the Planck constant, c is the light velocity, and  $L_{\text{light}}$  is the incident light intensity.

 $D^*$  is used to estimate the signal-to-noise ratio of photodetectors. The  $D^*$  of PPDs is calculated using the following Eq. S2:

$$D^{*}(\lambda) = \frac{R(\lambda)}{\sqrt{2q \cdot J_{d}}}$$
(Jones) (S2)

where q is the absolute value of electron charge  $(1.6 \times 10^{-19} \text{ Coulombs})$ . From the equation, it is obvious that the higher responsivity is desirable for lower  $J_d$ .

The hole-only devices with a configuration of Ag/PEDOT : PSS/Active layers/PEDOT : PSS/Ag and electron-only devices with a configuration of Mg : Ag/Active layers/Mg : Ag were fabricated, respectively. The hole mobility in the hole-only devices and the electron mobility in the electron-only devices can be calculated using Mott-Gurney law as Eq. S3.

$$J = \frac{9}{8} \varepsilon \varepsilon_0 \mu \frac{V^2}{d^3}$$
(S3)

where  $\varepsilon$  is the relative permittivity of organic materials assumed to be 3, and  $\varepsilon_0$  is the vacuum dielectric constant of  $8.85 \times 10^{-12}$  F/m. *V* is the voltage, and *d* is the thickness of active layer.

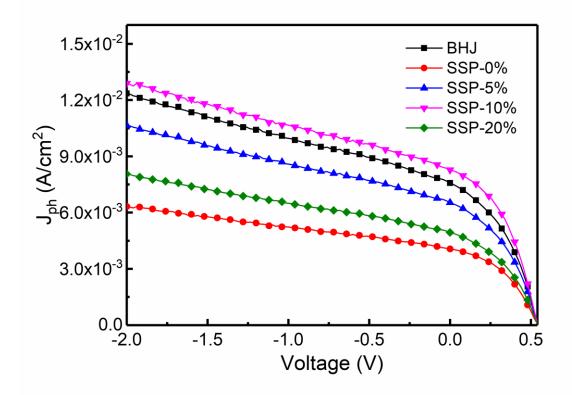
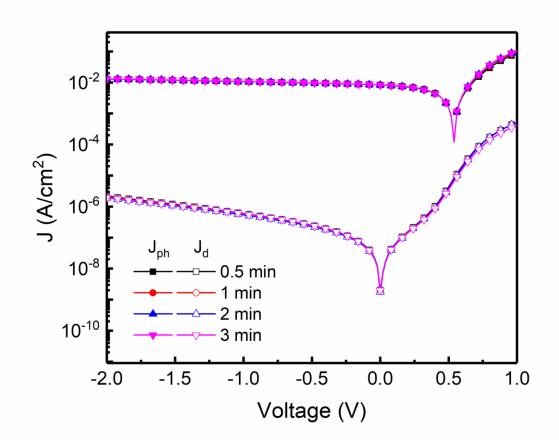
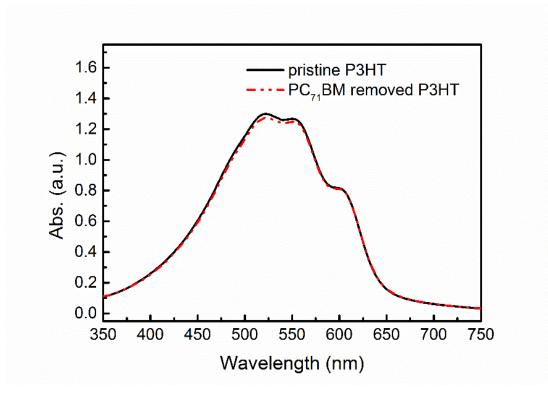


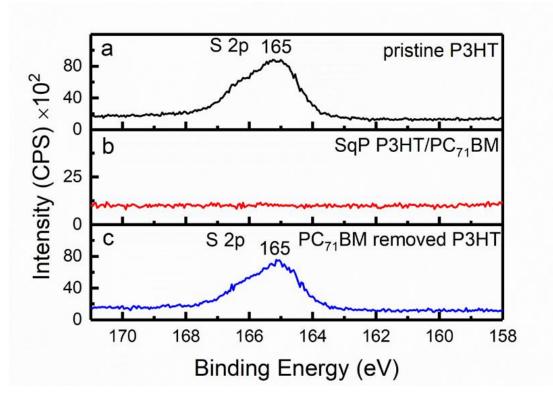
Figure S1. J-V characteristics of PPDs under AM 1.5 light illumination.



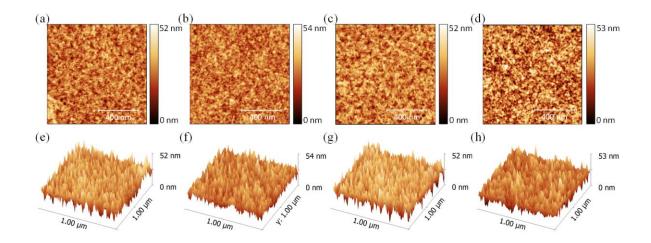
**Figure S2**. Semi-log *J-V* characteristics of SSP-10% PPDs with different swelling time from 0.5, 1, 2, to 3 min in dark and under AM 1.5 light illumination.



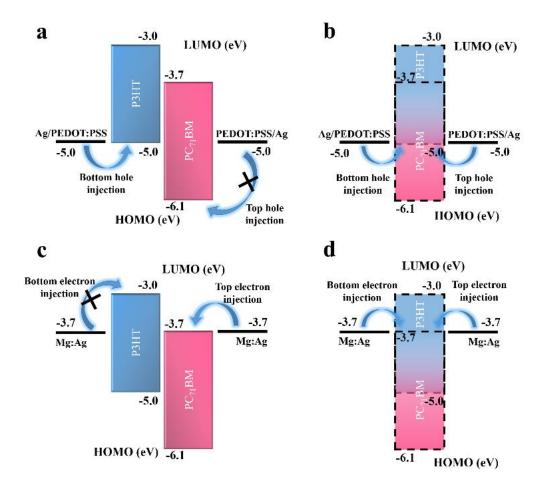
**Figure S3**. UV-visible absorption spectra of pristine P3HT film and an P3HT film onto which a  $PC_{71}BM$  layer had been spun from 2-CP : ODCB (9 : 1) and then subsequently removed by spin coating the bilayer with 2-CP, which is marked as "PC<sub>71</sub>BM removed P3HT" in the inset.



**Figure S4**. XPS spectra (counts per second, cps vs. binding energy, B.E.) of the S 2p peaks for (a) pristine P3HT, (b) SSP P3HT/PC<sub>71</sub>BM, and (c) PC<sub>71</sub>BM removed P3HT films on silicon/silicon oxide substrates. The XPS data were taken at a take-off angle of 90° for all the films.



**Figure S5** AFM height images  $(1 \ \mu m \times 1 \ \mu m)$  of SSP-10% P3HT underlayers with different soaking times from (a) 0.5 min, (b) 1 min, (c) 2min, to (d) 3 min. The PC<sub>71</sub>BM layers on P3HT films were removed by spin coating 2-CP on them. The corresponding three-dimensional (3D) images are Figure e, f, g, and h.



**Figure S6**. Schematic energy level diagrams of (a) SSP-10% hole-only device under bottom and top hole injection, (b) BHJ hole-only device under bottom and top hole injection, (c) SSP-10% electron-only device under bottom and top electron injection, and BHJ electron-only device under bottom and top electron injection.

**Table S1.** Photocurrent density, dark current density, and on/off current ratio of SSP-10% PPDs withdifferent swelling time at -0.5 V.

Soaking time (min)	$J_{\rm ph}({\rm A/cm}^2)$	$J_{\rm d}$ (A/cm <sup>2</sup> )	On/off current ratio
0.5	9.65×10 <sup>-3</sup>	2.48×10 <sup>-7</sup>	3.89×10 <sup>4</sup>
1	9.62×10 <sup>-3</sup>	2.45×10 <sup>-7</sup>	3.93×10 <sup>4</sup>
2	9.65×10 <sup>-3</sup>	2.49×10 <sup>-7</sup>	3.88×10 <sup>4</sup>
3	9.69×10 <sup>-3</sup>	2.51×10 <sup>-7</sup>	3.86×10 <sup>4</sup>

PPD	EQE at 380 nm (%)	EQE at 470 nm (%)	EQE at 550 nm (%)	EQE at 620 nm (%)
BHJ	49.6	62.3	63.8	37.8
SSP-0%	24.5	32.0	34.8	22.9
SSP-10%	48.0	62.7	68.2	49.3

 Table S2. EQE of PPDs to UV, blue, green and red lights at -0.5 V.

PPD	<i>R</i> at 380 nm (A/W)	<i>R</i> at 470 nm (A/W)	<i>R</i> at 550 nm (A/W)	<i>R</i> at 620 nm (A/W)
BHJ	0.152	0.236	0.283	0.189
SSP-0%	0.075	0.121	0.154	0.114
SSP-10%	0.147	0.238	0.302	0.246

**Table S3**. *R* of PPDs to UV, blue, green and red lights at -0.5 V.

PPD	$D^*$ at 380 nm	$D^*$ at 470 nm	<i>R</i> at 550 nm	<i>R</i> at 620 nm
	(Jones)	(Jones)	(Jones)	(Jones)
BHJ	$1.24\times10^{11}$	$1.93 \times 10^{11}$	$2.31 \times 10^{11}$	$1.54 \times 10^{11}$
SSP-0%	$3.54 \times 10^{11}$	$5.73 \times 10^{11}$	$7.29 \times 10^{11}$	$5.40  imes 10^{11}$
SSP-10%	$5.96 \times 10^{11}$	$9.64 \times 10^{11}$	$1.23 \times 10^{12}$	$9.99  imes 10^{11}$

**Table S4**.  $D^*$  of PPDs to UV, blue, green and red lights at -0.5 V.